NSN 5961-01-414-5833

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Inclosure Material:

Metal

Internal Configuration:

Field effect

Joint Electronic Device Engineering Council/jedec/case Outline Designation:

To-236ab

Mounting Method:

Terminal

Semiconductor Material:

Silicon

Voltage Rating In Volts Per Characteristic:

30.0 drain to source voltage

Current Rating Per Characteristic:

10.00 milliamperes gate current

Terminal Type And Quantity:

3 bonding pad

Shelf Life:

N/a

Unit Of Measure:

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Demilitarization:

No

Fiig:

A110a0